

650V Super Junction Power MOSFET

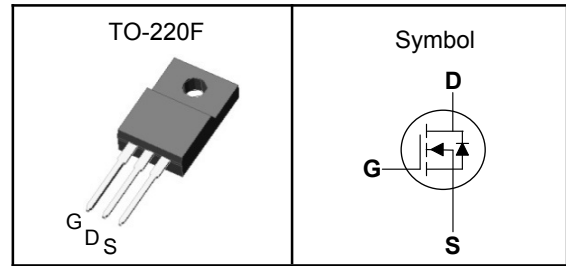
Features

- Low drain-source on-resistance: $R_{DS(ON)}=0.58\Omega(\text{typ})$
- Easy to control gate switching
- Enhancement mode: $V_{th} = 2$ to $4V$
- 100% avalanche tested
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger, Lighting

Pin Description



V_{DSS}	650	V
$R_{DS(ON)-Typ}$	580	m Ω
I_D	8	A

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V_{DSS}	Drain-Source Voltage	650	V
V_{GSS}	Gate-Source Voltage	± 30	V
T_J	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Single Pulse Avalanche Energy ³	156	mJ
$I_{DM}^{①}$	300 μs Pulse Drain Current Tested	14	A
I_D	Continuous Drain Current	8	A
P_D	Maximum Power Dissipation	25.5	W
I_{AS}	Avalanche Current	5	A
dv/dt	MOSFET dv/dt ruggedness, $V_{DS} = 0 \dots 400V$	50	V/ns
	Reverse diode dv/dt ³ $V_{DS}=0 \dots 400V, I_{SD} \leq I_D$	15	

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}^{③}$	Thermal Resistance Junction-Ambient ¹ (Max)	49	$^\circ\text{C}/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹ (Max)	4.9	$^\circ\text{C}/W$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C .

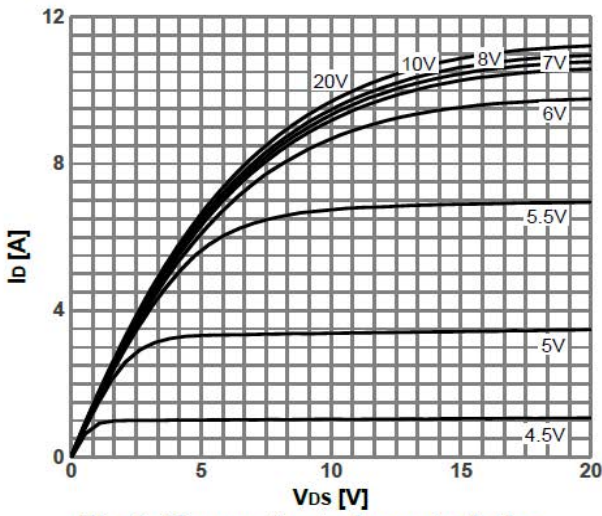
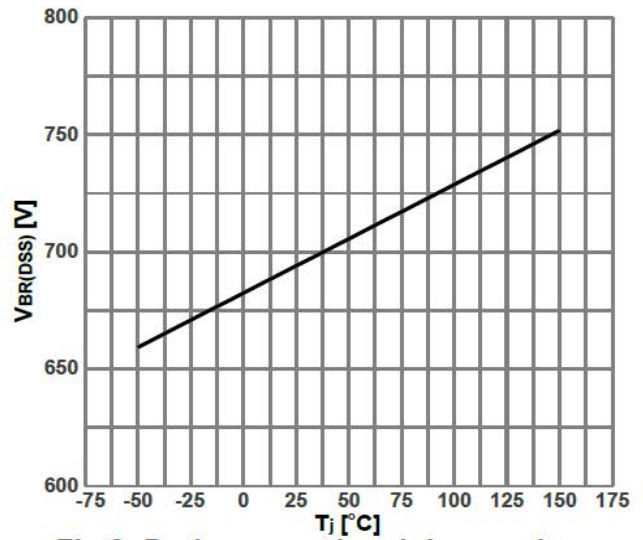
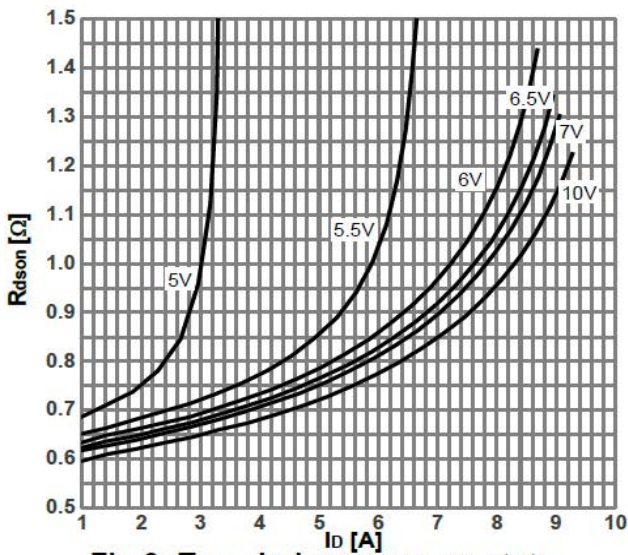
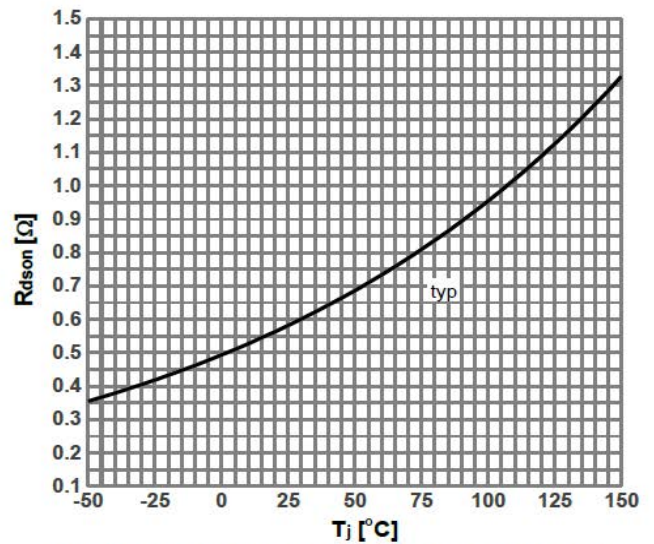
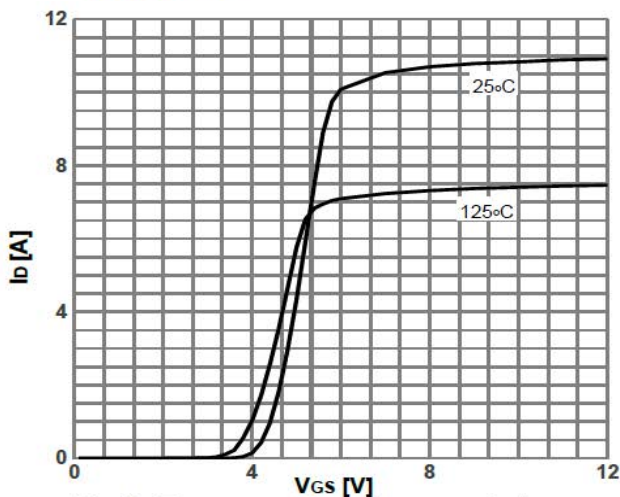
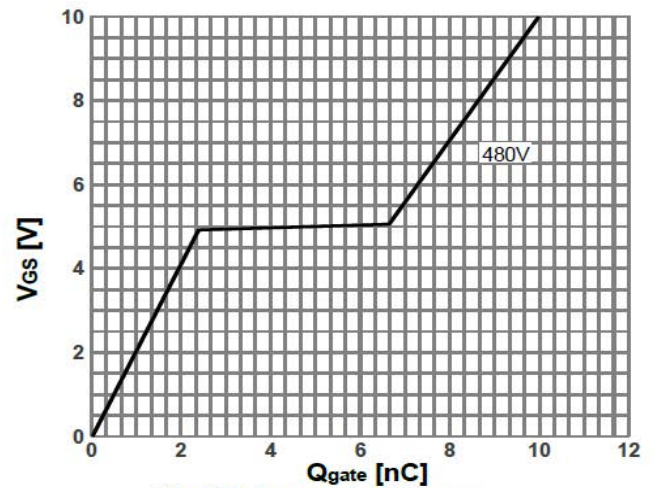
Note ③ : Surface Mounted on 1in^2 FR-4 board with 1oz.

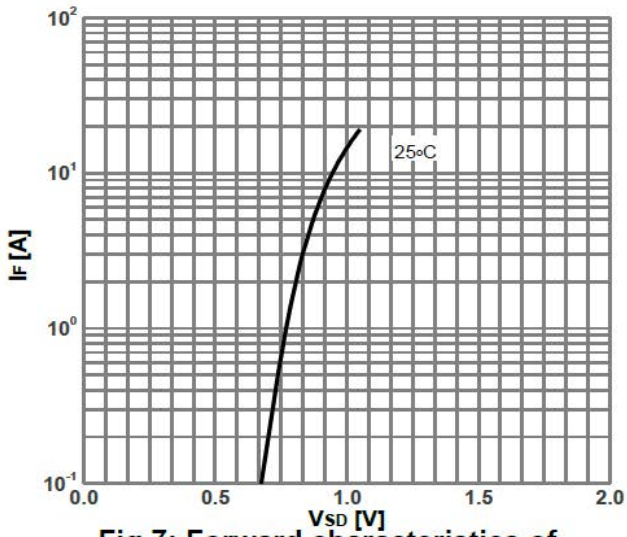
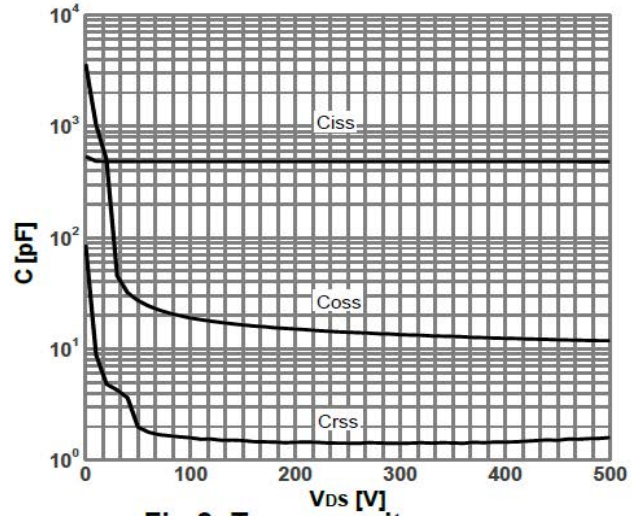
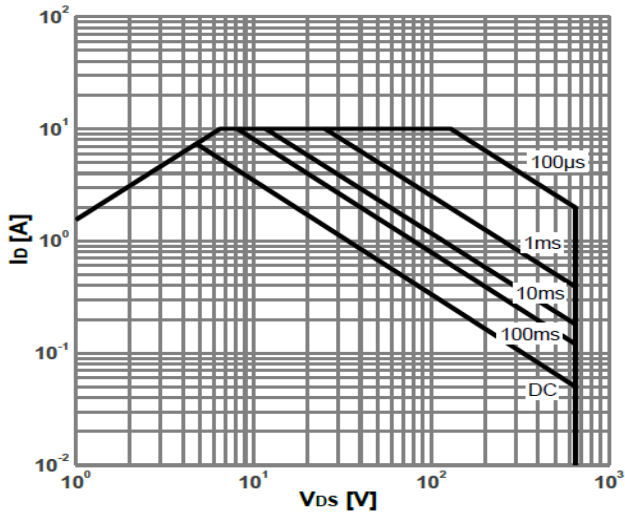
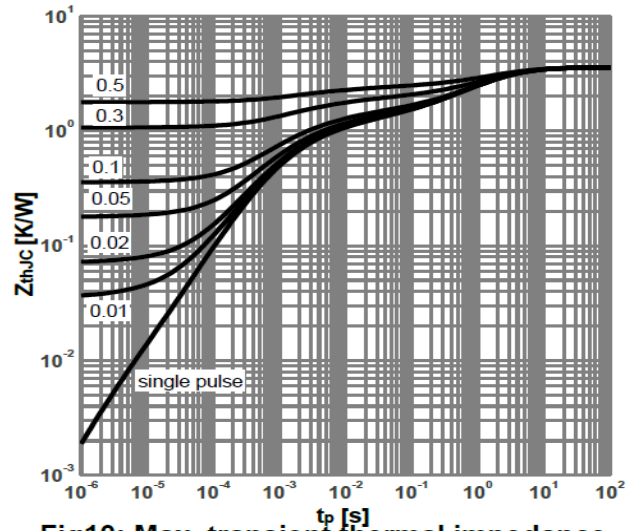
**650V Super Junction Power MOSFET****Electrical Characteristics** ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	650	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	---	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=3.2A$	---	580	650	m Ω
Dynamic Characteristics ^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=50V,$ Freq.=1MHz	---	142	---	pF
C_{oss}	Output Capacitance		---	28	---	
C_{rss}	Reverse Transfer Capacitance		---	1.2	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=400V, V_{GS}=10V,$ $I_D=3.2A$	---	130	---	nS
T_r	Turn-on Rise Time		---	54	---	
$T_{d(off)}$	Turn-off Delay Time		---	350	---	
T_f	Turn-off Fall Time		---	90	---	
Q_g	Total Gate Charge	$V_{DD}=480V, V_{GS}=10V,$ $I_D=3.2A$	---	10.4	---	nC
Q_{gs}	Gate-Source Charge		---	9	---	
Q_{gd}	Gate-Drain Charge		---	4	---	
Source-Drain Characteristics ($T_J=25^\circ\text{C}$)						
V_{SD} ^④	Diode Forward Voltage	$V_G=0V, I_S=3.2A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$V_R=400V, I_F=3.2A,$ $di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	155	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.15	---	nC

Note ④ : Pulse test (pulse width \leq 300 μs , duty cycle \leq 2%).

Note ⑤ : Guaranteed by design, not subject to production testing.

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Typical Characteristics

Fig 1: Typ. output characteristics

Fig 2: Drain-source breakdown voltage

Fig 3: Typ. drain-source on-state resistance

Fig 4: drain-source on-state resistance

Fig 5: Typ. transfer characteristics

Fig 6: Typ. gate charge

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Fig 7: Forward characteristics of reverse diode

Fig 8: Typ. capacitances

Fig 9: Safe operating area

Fig 10: Max. transient thermal impedance

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TO-220F Package Outline Data
